Power LDMOS transistor Rev. 3 — 24 November 2017

Product profile 1.

1.1 General description

400 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 1452 MHz to 1511 MHz.

Table 1. **Typical performance**

Typical RF performance at T_{case} = 25 °C in an asymmetrical Doherty production test circuit. V_{DS} = 32 V; I_{Dq} = 810 mA (main); $V_{GS(amp)peak}$ = 0.5 V, unless otherwise specified.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	ησ	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1452 to 1511	32	93	16.5	48	-35 <mark>[1]</mark>

[1] Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 1452 MHz to 1511 MHz frequency range

2. Pinning information

Table 2. P	inning		
Pin	Description	Simplified outline	Graphic symbol
1	drain2 (peak)		0.7
2	drain1 (main)		2, 7
3	gate1 (main)	5	
4	gate2 (peak)		35
5	source	[1]	
6	video decoupling (peak)		۳ <u>۲</u>
7	video decoupling (main)		1, 6 aaa-014884

[1] Connected to flange.

3. Ordering information

Table 3.Ordering information

Type number	Package				
	Name	Description	Version		
BLC9G15LS-400AVT	-	air cavity plastic earless flanged package; 6 leads	SOT1258-1		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		-	65	V
V _{GS(amp)main}	main amplifier gate-source voltage		-6	+13	V
V _{GS(amp)peak}	peak amplifier gate-source voltage		-6	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C
T _{case}	case temperature	operating [1]	-40	+125	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	V _{DS} = 32 V; I _{Dq} = 980 mA (main); V _{GS(amp)peak} = 0,4 V; T _{case} = 80 °C		
		P _L = 93 W	0.31	k/W
		P _L = 117 W	0.29	k/W

6. Characteristics

 $T_j = 25 \ \mathcal{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	vice					
V _{(BR)DSS}	drain-source breakdown voltage	V _{GS} = 0 V; I _D = 1.62 mA	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 162 mA	1.5	2.0	2.5	V
V _{GSq}	gate-source quiescent voltage	V _{DS} = 32 V; I _D = 810 mA	1.65	2.15	2.65	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	2.8	μA
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	32	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 8.1 A	-	11.5	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I _D = 5.67 A	-	85	149	mΩ
Peak dev	vice	1				
V _{(BR)DSS}	drain-source breakdown voltage	V _{GS} = 0 V; I _D = 3.0 mA	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 300 mA	1.5	2.0	2.5	V
V _{GSq}	gate-source quiescent voltage	V _{DS} = 32 V; I _D = 1500 mA	1.65	2.15	2.65	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	2.8	μA
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	52	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
g fs	forward transconductance	V _{DS} = 10 V; I _D = 15 A	-	20.5	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I _D = 10.5 A	-	46	85	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; $f_1 = 1455$ MHz; $f_2 = 1508.5$ MHz; RF performance at $V_{DS} = 32$ V; $I_{Dq} = 810$ mA (main); $V_{GS(amp)peak} = 0.5$ V; $T_{case} = 25$ °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1452 MHz to 1511 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G _p	power gain	P _{L(AV)} = 93 W	15	16.2	-	dB
RL _{in}	input return loss	P _{L(AV)} = 93 W	-	-15	-10	dB
η_D	drain efficiency	P _{L(AV)} = 93 W	46.5	51	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 93 W	-	-34	-29	dBc

Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f = 1508.5 MHz; RF performance at V_{DS} = 32 V; I_{Dq} = 810 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at a frequency of 1511 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PARO	output peak-to-average ratio	P _{L(AV)} = 110 W	6.3	6.9	-	dB
$P_{L(M)}$	peak output power	P _{L(AV)} = 110 W	460	540	-	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC9G15LS-400AVT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 810 mA; $V_{GS(amp)peak}$ = 0.5 V; f = 1454.5 MHz; P_L = 126 W (5 dB OBO); 1-carrier W-CDMA; 100 % clipping.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 810 mA (main); V_{DS} = 30 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	PL ^[2]	η _D [2]	G _p [2]				
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)				
Maximu	Maximum power load								
1440	1.0 – j4.8	0.9 – j3.4	245	53.5	18.0				
1480	1.4 – j5.3	0.9 – j3.7	245	55.6	18.3				
1510	1.5 – j5.7	1.0 – j4.0	245	57.1	18.7				
Maximu	m drain efficienc	y load							
1440	1.0 – j4.8	2.5 – j3.1	170	71.8	21.4				
1480	1.4 – j5.3	2.5 – j2.9	153	72.3	21.8				
1510	1.5 – j5.7	2.5 – j3.0	153	71.2	21.9				

[1] Z_S and Z_L defined in Figure 1.

[2] At 3 dB gain compression.

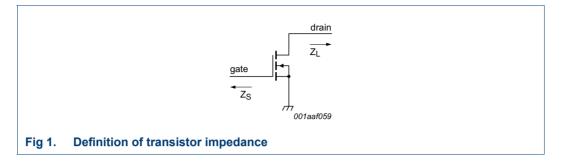
Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 1800 mA (peak); V_{DS} = 30 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _L [2]	η <mark>ρ ^[2]</mark>	G _p [2]				
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)				
Maximur	Maximum power load								
1440	2.0 – j7.6	1.5 – j3.4	390	54.3	19.4				
1480	3.0 – j8.0	1.6 – j3.4	400	57.0	19.7				
1510	2.8 – j9.2	1.8 – j3.6	390	55.4	19.8				
Maximur	n drain efficiency	load							
1440	2.0 – j7.6	3.1 – j1.4	255	67.3	22.4				
1480	3.0 – j8.0	2.5 – j1.7	271	68.3	22.3				
1510	2.8 – j9.2	2.2 – j1.9	283	67.2	22.4				

[1] Z_S and Z_L defined in Figure 1.

[2] At 3 dB gain compression.



7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main at 1 : 1 load

Measured load-pull data of main device; I_{Dq} = 810 mA (main); V_{DS} = 30 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _{L(3dB)} [2]	η <mark>ρ ^[2]</mark>	G _p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1440	1.0 – j4.8	1.50 – j4.2	220	45	19.5
1480	1.4 – j5.3	1.40 – j3.7	230	46	19.6
1510	1.5 – j5.7	1.38 – j3.5	220	47	20.4

[1] Z_S and Z_L defined in Figure 1.

[2] At P_{L(AV)} = 93 W.

Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device; I_{Dq} = 810 mA (main); V_{DS} = 30 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _{L(3dB)} [2]	ղ ը ^[2]	G _p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1440	1.0 – j4.8	3.4 – j3.5	140	65	22.0
1480	1.4 – j5.3	3.3 – j3.2	125	65	22.4
1510	1.5 – j5.7	3.3 – j3.0	120	64	23.2

[1] Z_S and Z_L defined in Figure 1.

[2] At P_{L(AV)} = 93 W.

Table 13. Typical impedance of peak device at 1 : 1 load

Measured load-pull data of peak device; I_{Dq} = 1500 mA (peak); V_{DS} = 30 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _{L(3dB)} [2]	η <mark>ρ ^[2]</mark>	G _p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1410	2.0 – j7.6	2.0 – j4.2	380	31	19.0
1480	3.0 – j8.0	1.9 – j3.6	390	32.5	19.6
1520	2.8 – j9.2	1.9 – j3.3	380	33	20.3

[1] Z_S and Z_L defined in Figure 1.

[2] At P_{L(AV)} = 93 W.

Table 14. Off-state impedances of peak device

f	Z _{off}
(MHz)	(Ω)
1410	1.22 – j3.50
1480	0.57 – j1.30
1520	0.43 – j0.63

7.4 Test circuit

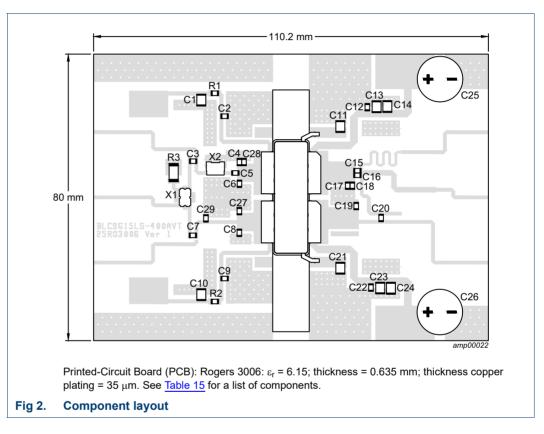


Table 15.List of components

See Figure 2 for component layout.

Component	Description	Value	Remarks
•	•		
C1, C10, C11, C13, C14, C21, C23, C24	multilayer ceramic chip capacitor	4.7 μF	Murata GRM32ER71H475KA88L
C2, C3, C5, C7, C9, C12, C15, C16, C20, C22	multilayer ceramic chip capacitor	18 pF	Murata Hi-Q 0805
C4,C6, C27, C28	multilayer ceramic chip capacitor	2.0 pF	Murata Hi-Q 0805
C8,C17, C18	multilayer ceramic chip capacitor	1.8 pF	Murata Hi-Q 0805
C19	multilayer ceramic chip capacitor	2.7 pF	Murata Hi-Q 0805
C25, C26	electrolytic capacitor	470 μF	63 V
C29	multilayer ceramic chip capacitor	0.3 pF	ATC 100A 0805
R1, R2	SMD resistor	4.7 Ω, 1 %	0805

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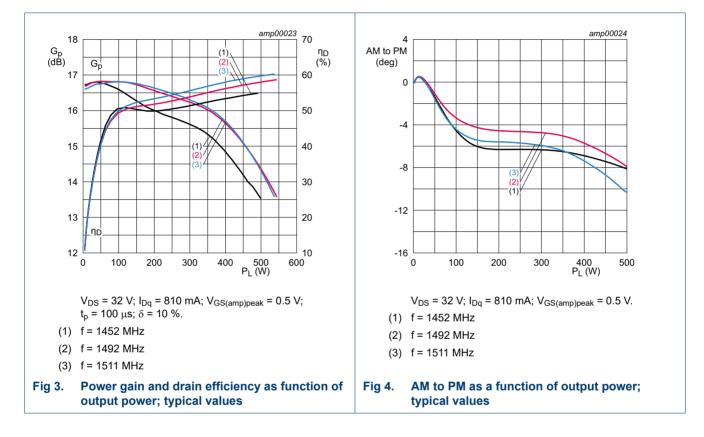
Table 15. List of components ...continued

See Figure 2 for component layout.

Component	Description	Value	Remarks
R3	SMD resistor	50 Ω, 25 W	Anaren C16A50Z4
X1	hybrid coupler	2 dB, 90°	Anaren X3C20F1-02S
X2	attenuator	1 dB	Anaren D10AAXXZ4

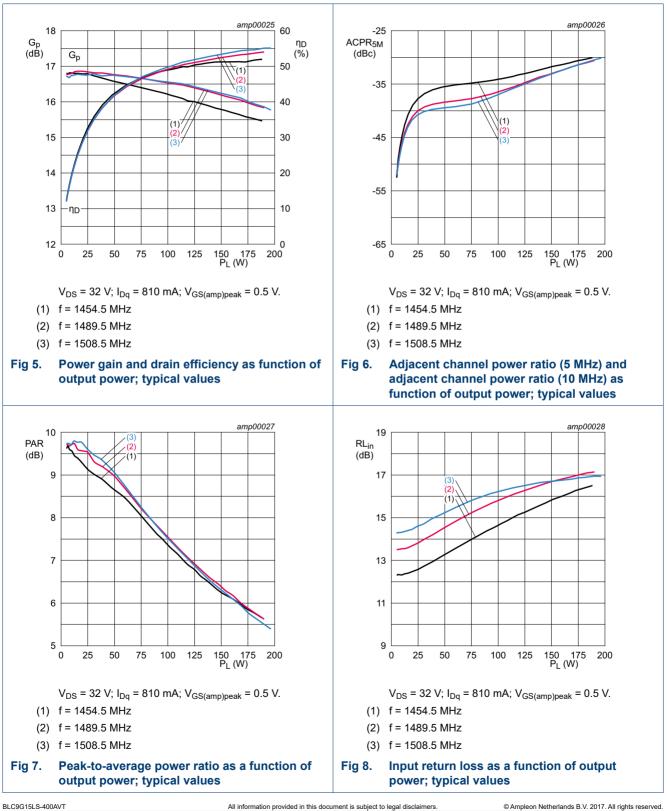
7.5 Graphical data

7.5.1 Pulsed CW



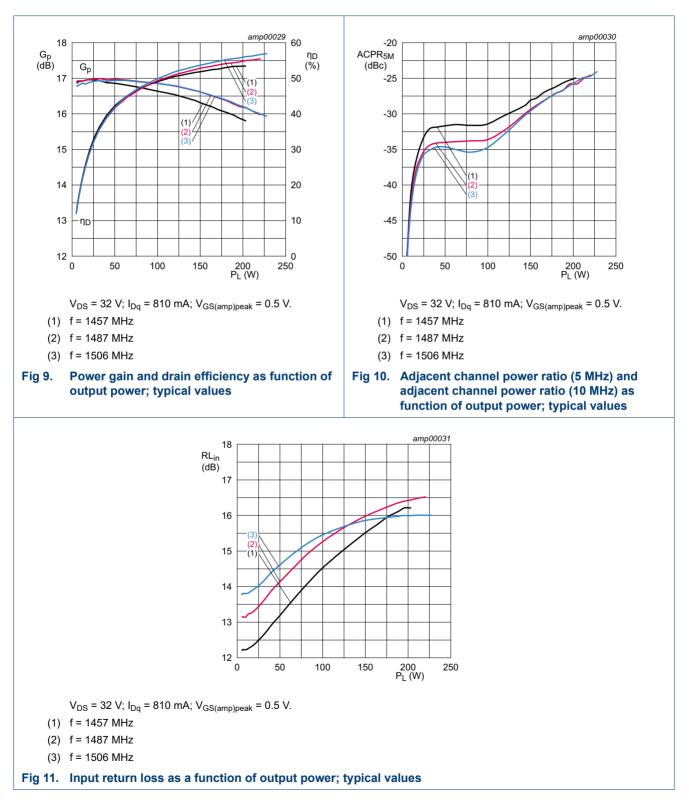
7.5.2 1-Carrier W-CDMA

PAR = 9.6 dB per carrier at 0.01 % probability on the CCDF; 3GPP test model 1 with 64 DPCH (100 % clipping).



7.5.3 2-Carrier W-CDMA

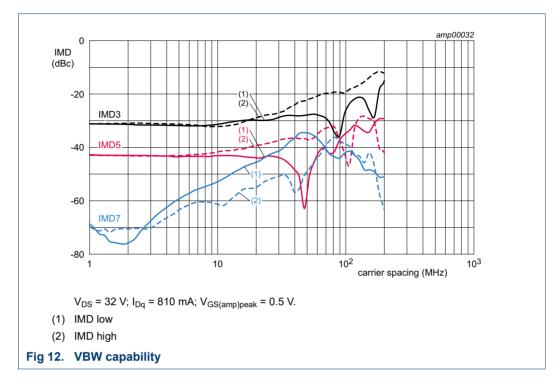
PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1 with 64 DPCH (46 % clipping).



Product data sheet

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7.5.4 2-Tone VBW



BLC9G15LS-400AVT

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Power LDMOS transistor

8. Package outline

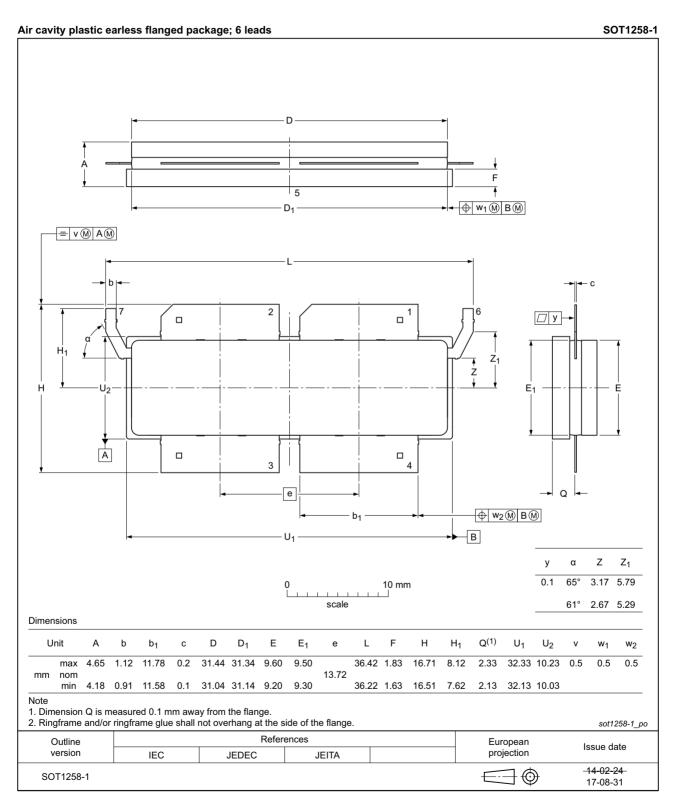


Fig 13. Package outline SOT1258-1

BLC9G15LS-400AVT

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 16.ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

[1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 17. Abbreviations

Acronym	Description			
3GPP	3rd Generation Partnership Project			
AM	Amplitude Modulation			
CCDF	Complementary Cumulative Distribution Function			
CW	Continuous Wave			
DPCH	Dedicated Physical CHannel			
ESD	ElectroStatic Discharge			
LDMOS	Laterally Diffused Metal-Oxide Semiconductor			
MTF	Median Time to Failure			
OBO	Output Back Off			
PAR	Peak-to-Average Ratio			
PM	Phase Modulation			
SMD	Surface Mounted Device			
VBW	Video Bandwidth			
VSWR	Voltage Standing Wave Ratio			
W-CDMA	Wideband Code Division Multiple Access			
PM SMD VBW VSWR	Phase Modulation Surface Mounted Device Video Bandwidth Voltage Standing Wave Ratio			

11. Revision history

Table 18. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G15LS-400AVT v.3	20171124	Product data sheet	-	BLC9G15LS-400AVT v.2
Modifications:	• Table 2 on page 2: changed simplified version drawing SOT1258-3 to SOT1258-1			
	• Table 3 on pa	ige 2: changed version SOT1	258-3 to SOT1258-1	
	• Figure 13 on	page 11: changed package o	utline drawing SOT1	258-3 to SOT1258-1
BLC9G15LS-400AVT v.2	20161202	Product data sheet	-	BLC9G15LS-400AVT v.1
BLC9G15LS-400AVT v.1	20160317	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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BLC9G15LS-400AVT

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